



650V N-ch Planar MOSFET

Lead Free Package and Finish

General Features

- RoHS Compliant
- $R_{DS(ON),typ.}=3.5\Omega@V_{GS}=10V$
- Low Gate Charge Minimize Switching Loss
- Fast Recovery Body Diode

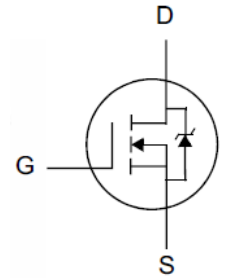
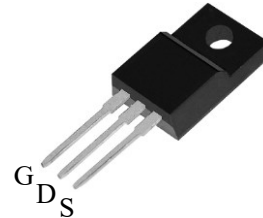
BV_{DSS}	$R_{DS(ON),typ.}$	I_D
650V	3.5Ω	2A

Applications

- Adaptor
- Charger
- SMPS Standby Power

Ordering Information

Part Number	Package	Brand
PTA02N65	TO-220F	



TO-220F

Package No to Scale

Absolute Maximum Ratings

$T_C=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	PTA02N65	Unit
V_{DSS}	Drain-to-Source Voltage	650	V
V_{GSS}	Gate-to-Source Voltage	±30	
I_D	Continuous Drain Current	2	A
I_{DM}	Pulsed Drain Current at $V_{GS}=10V$	8	
E_{AS}	Single Pulse Avalanche Energy	80	mJ
P_D	Power Dissipation	27	W
	Derating Factor above 25°C	0.22	W/°C
T_L	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	°C
$T_J \& T_{STG}$	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	PTA02N65	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	4.55	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62	



Electrical Characteristics

OFF Characteristics

$T_J = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	650	--	--	V	$V_{GS}=0V, I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	--	--	1	μA	$V_{DS}=650V, V_{GS}=0V$
		--	--	100		$V_{DS}=520V, V_{GS}=0V, T_J=125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Current	--	--	+100	nA	$V_{GS}=+30V, V_{DS}=0V$
		--	--	-100		$V_{GS}=-30V, V_{DS}=0V$

ON Characteristics

$T_J = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	3.5	4.5	Ω	$V_{GS}=10V, I_D=1A$
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance	--	343	--	pF	$V_{GS}=0V, V_{DS}=25V, f=1.0MHz$
C_{rSS}	Reverse Transfer Capacitance	--	2.6	--		
C_{oss}	Output Capacitance	--	30	--		
Q_g	Total Gate Charge	--	6.95	--	nC	$V_{DD}=325V, I_D=2A, V_{GS}=0 \text{ to } 10V$
Q_{gs}	Gate-to-Source Charge	--	1.7	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	2.6	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	7.2	--	ns	$V_{DD}=325V, I_D=2A, V_{GS}=10V, R_g=9.1\Omega$
t_{rise}	Rise Time	--	4.2	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	17.7	--		
t_{fall}	Fall Time	--	16.8	--		

**Source-Drain Body Diode Characteristics** $T_J=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
I_{SD}	Continuous Source Current ^[2]	--	--	2	A	Integral pn-diode in MOSFET
I_{SM}	Pulsed Source Current ^[2]	--	--	8		
V_{SD}	Diode Forward Voltage	--	--	1.4	V	$I_S=2\text{A}$, $V_{GS}=0\text{V}$
t_{rr}	Reverse Recovery Time	--	104	--	ns	$V_{GS}=0\text{V}$ $I_F=I_S$, $di/dt=100\text{A}/\mu\text{s}$
Q_{rr}	Reverse Recovery Charge	--	241	--	nC	

Note:

[1] $T_J=+25^{\circ}\text{C}$ to $+150^{\circ}\text{C}$

[2] Pulse width $\leq 380\mu\text{s}$; duty cycle $\leq 2\%$.



Typical Characteristics

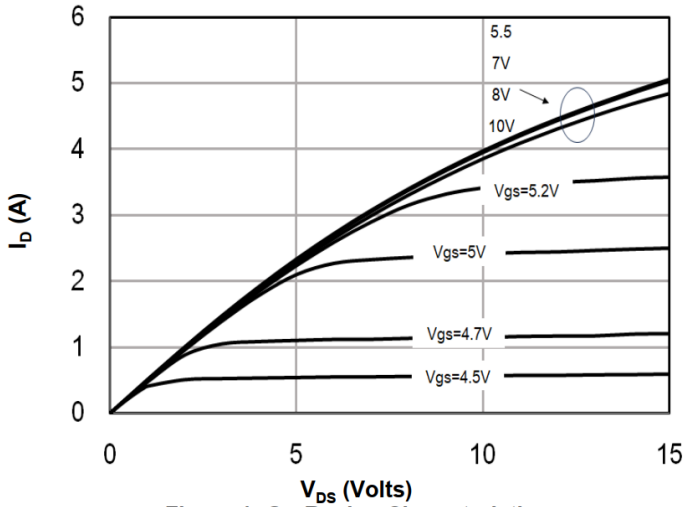


Figure 1: On-Region Characteristics

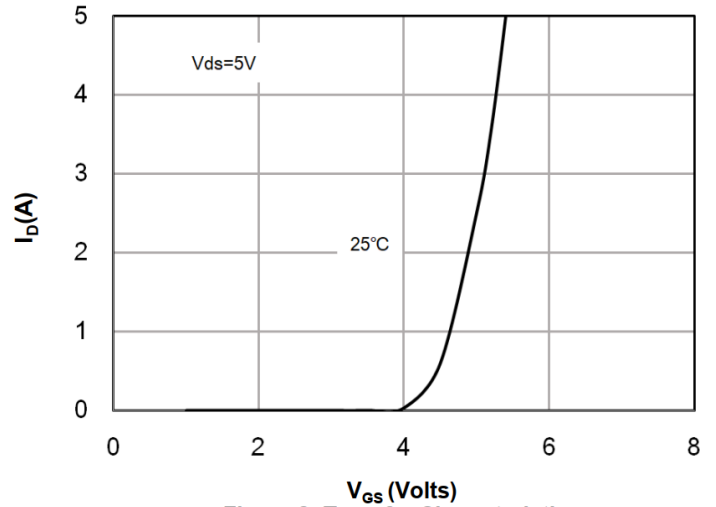


Figure 2: Transfer Characteristics

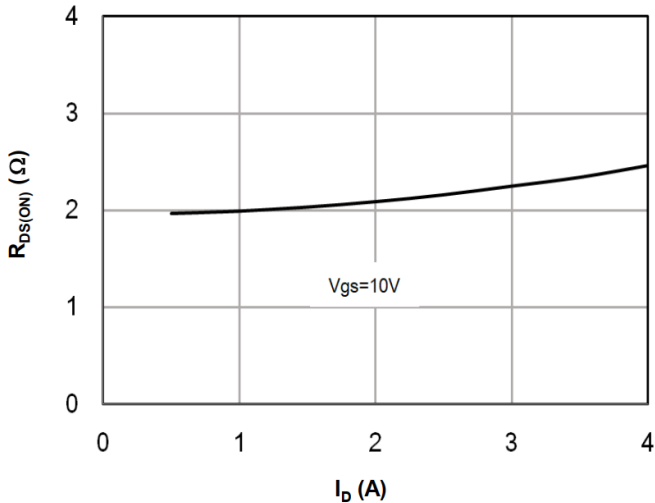


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

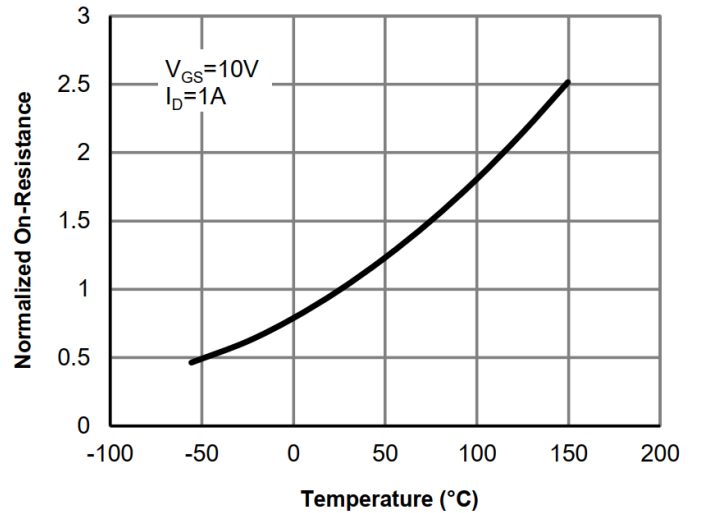


Figure 4: On-Resistance vs. Junction Temperature

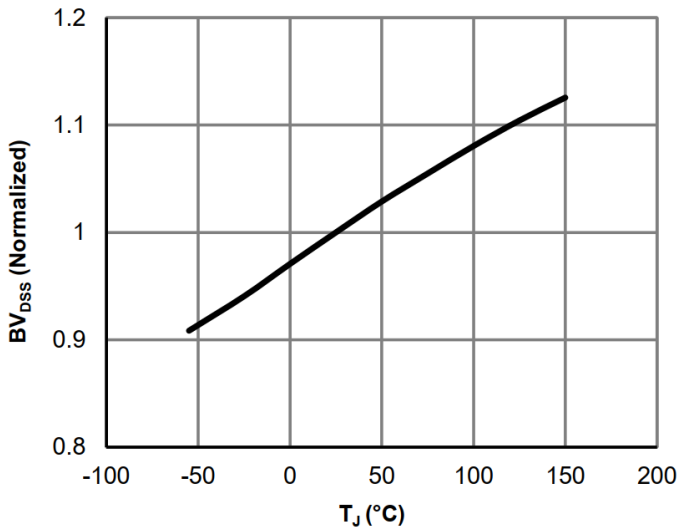


Figure 5: Break Down vs. Junction Temperature

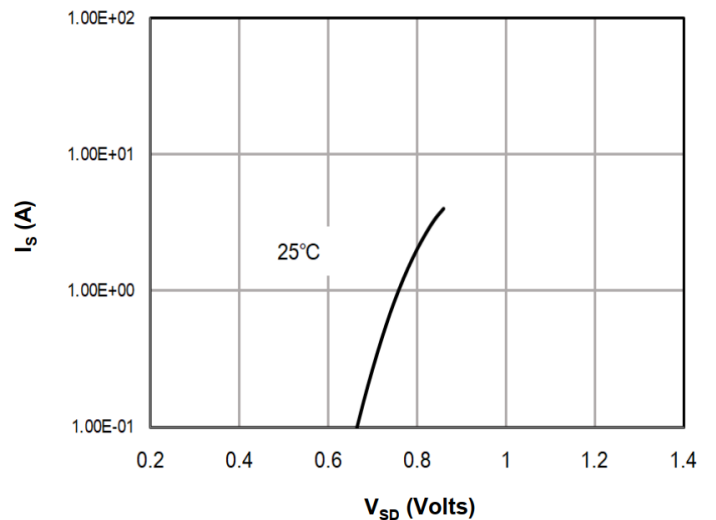


Figure 6: Body-Diode Characteristics

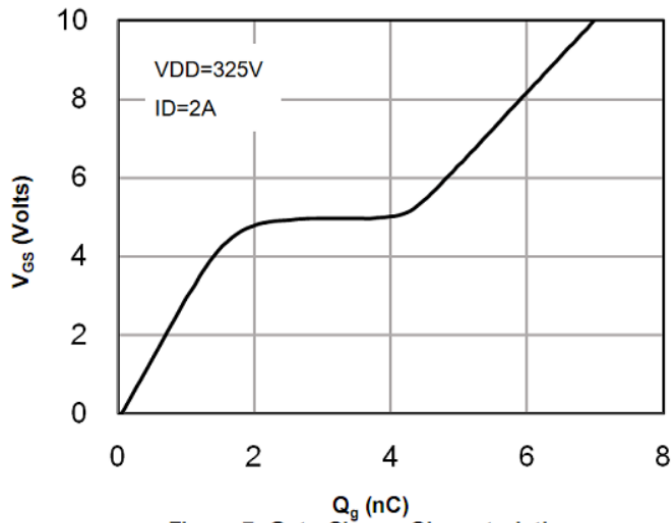


Figure 7: Gate-Charge Characteristics

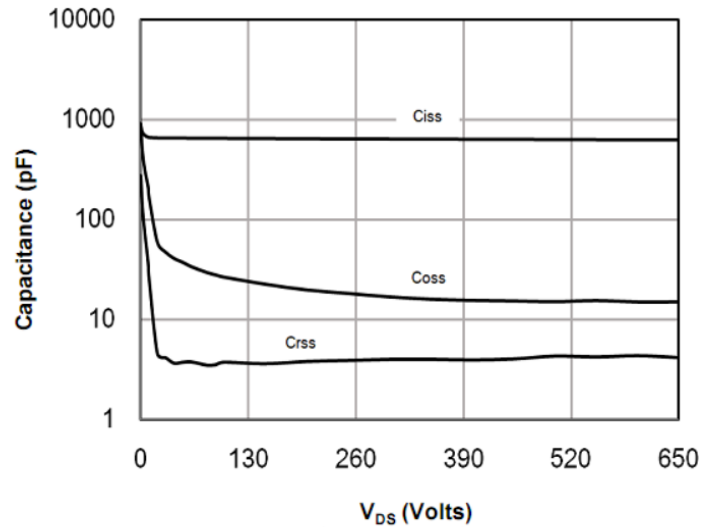


Figure 8: Capacitance Characteristics

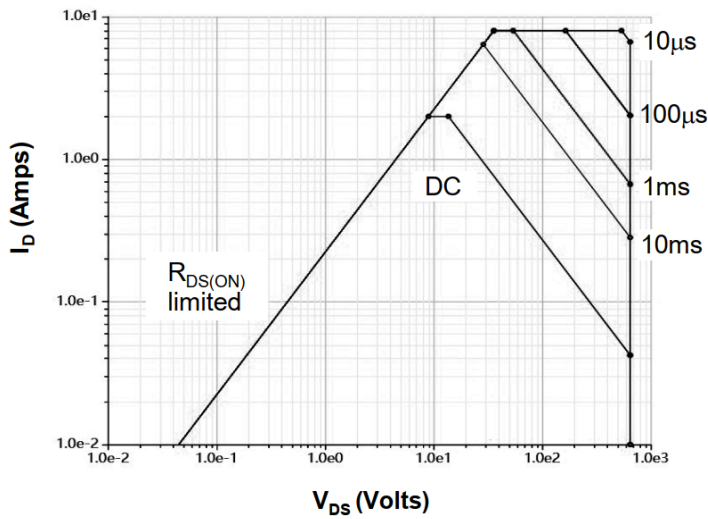


Figure 9: Maximum Forward Biased Safe Operating Area

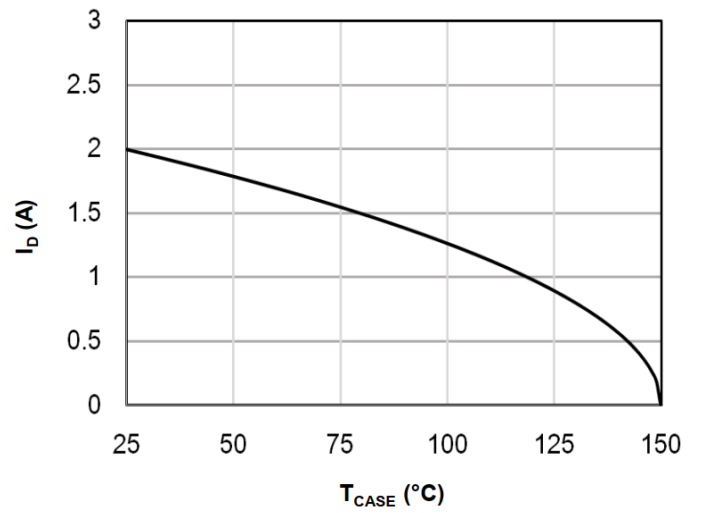


Figure 10: Tcase Temperature

Test Circuits and Waveforms

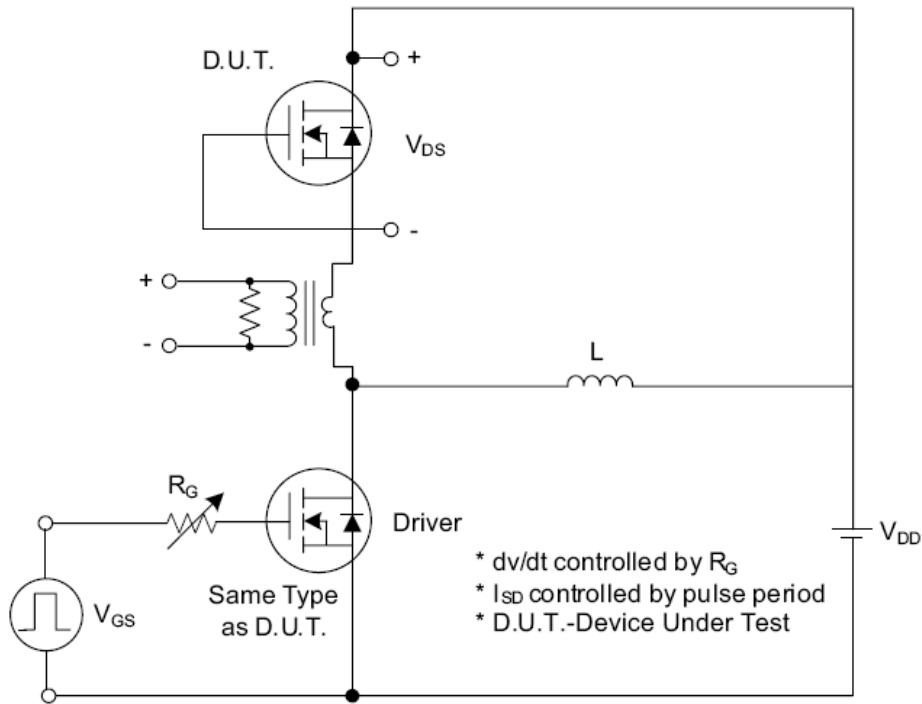


Fig. 1.1 Peak Diode Recovery dv/dt Test Circuit

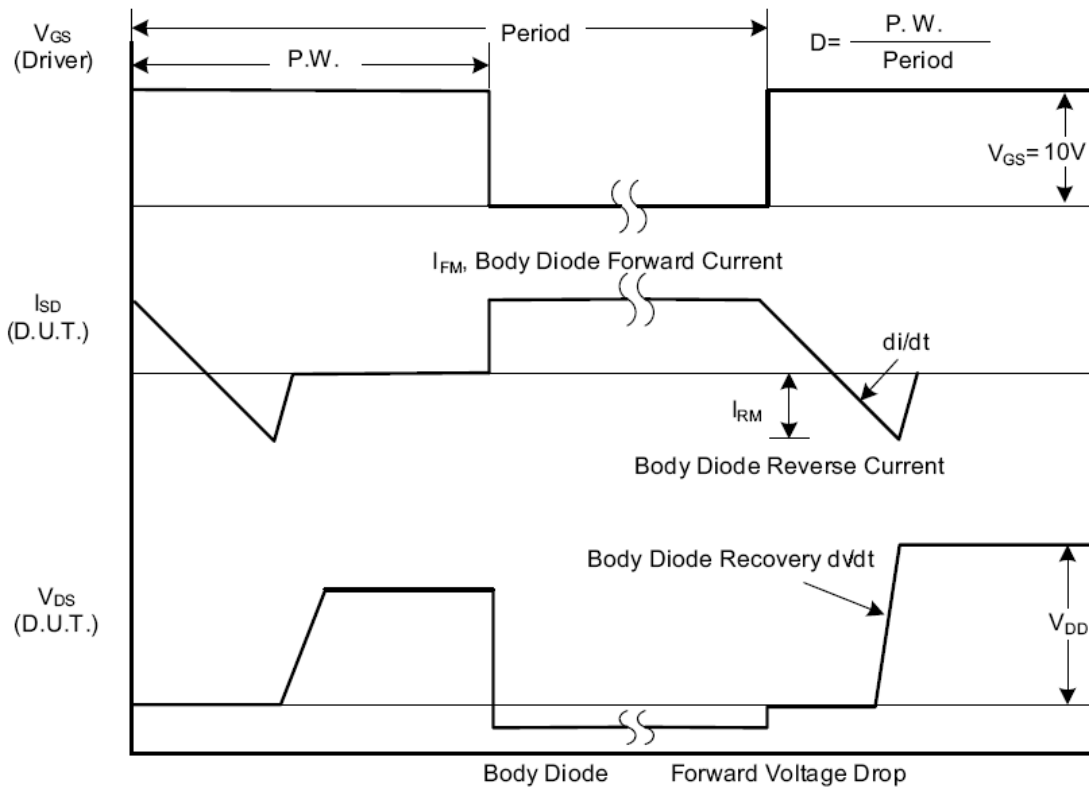


Fig. 1.2 Peak Diode Recovery dv/dt Waveforms

Test Circuits and Waveforms (Cont.)

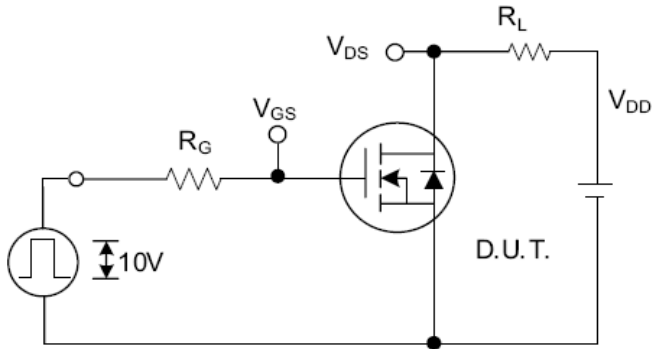


Fig. 2.1 Switching Test Circuit

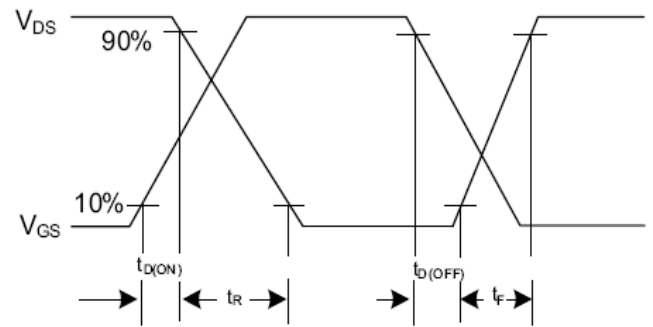


Fig. 2.2 Switching Waveforms

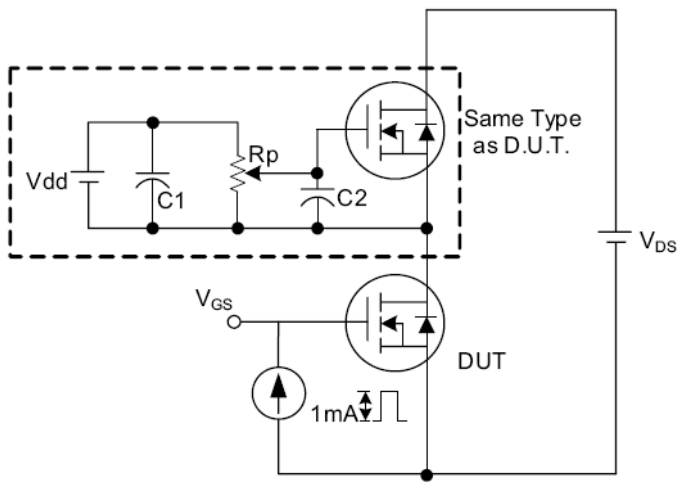


Fig. 3.1 Gate Charge Test Circuit

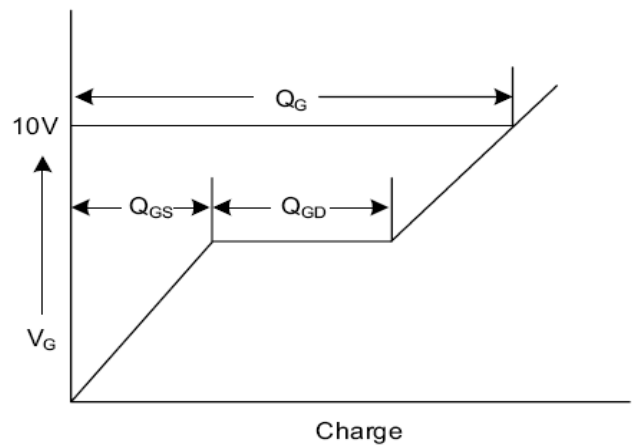


Fig. 3.2 Gate Charge Waveform

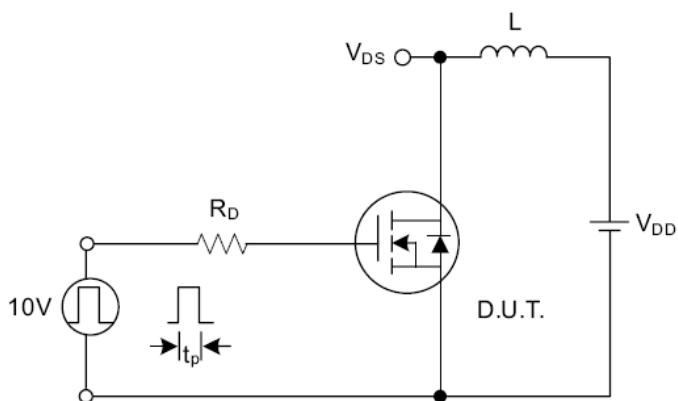


Fig. 4.1 Unclamped Inductive Switching Test Circuit

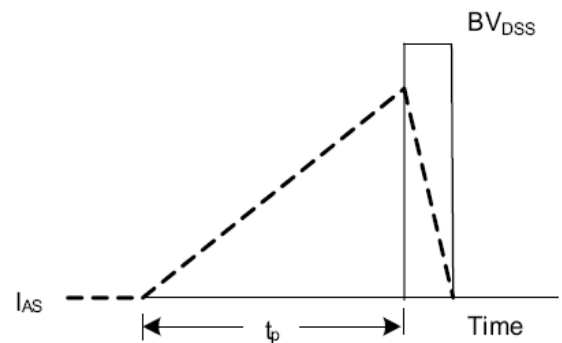


Fig. 4.2 Unclamped Inductive Switching Waveforms



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